Small Signal MOSFET 200 mAmps, 60 Volts

N-Channel TO-92

Features

- AEC Qualified
- PPAP Capable
- This is a Pb-Free Device*



Rating	Symbol	Value	Unit
Drain Source Voltage	V _{DSS}	60	Vdc
Drain-Gate Voltage (R _{GS} = 1.0 MΩ)	V_{DGR}	60	Vdc
Gate-Source Voltage - Continuous - Non-repetitive (t _p ≤ 50 μs)	V _{GS} V _{GSM}	±20 ±40	Vdc Vpk
Drain Current - Continuous - Pulsed	I _D I _{DM}	200 500	mAdc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	350 2.8	mW mW/°C
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/16" from case for 10 seconds	TL	300	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



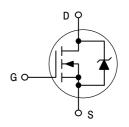
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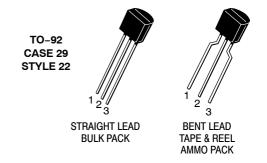
http://onsemi.com

200 mAMPS 60 VOLTS

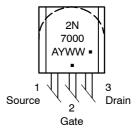
 $R_{DS(on)} = 5 \Omega$

N-Channel





MARKING DIAGRAM AND PIN ASSIGNMENT



A = Assembly Location

Y = Year WW = Work Week ■ Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

1

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

(V _{GS} = 0, I _D = 10 μAdc)				-
(\(\langle \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \				
$(V_{GS} = 0, I_D = 10 \mu\text{Adc})$	V _{(BR)DSS}	60	_	Vdc
Zero Gate Voltage Drain Current $ (V_{DS} = 48 \ Vdc, \ V_{GS} = 0) \\ (V_{DS} = 48 \ Vdc, \ V_{GS} = 0, \ T_J = 125^{\circ}C) $			1.0 1.0	μAdc mAdc
ward $(V_{GSF} = 15 \text{ Vdc}, V_{DS} = 0)$	I _{GSSF}	-	-10	nAdc
$(V_{DS} = V_{GS}, I_D = 1.0 \text{ mAdc})$	V _{GS(th)}	0.8	3.0	Vdc
ce $(V_{GS} = 10 \text{ Vdc}, I_D = 0.5 \text{ Adc})$ $(V_{GS} = 4.5 \text{ Vdc}, I_D = 75 \text{ mAdc})$	r _{DS(on)}	- -	5.0 6.0	Ω
$(V_{GS} = 10 \text{ Vdc}, I_D = 0.5 \text{ Adc})$ $(V_{GS} = 4.5 \text{ Vdc}, I_D = 75 \text{ mAdc})$	V _{DS(on)}	- -	2.5 0.45	Vdc
(V _{GS} = 4.5 Vdc, V _{DS} = 10 Vdc)	I _{d(on)}	75	-	mAdc
Forward Transconductance (V _{DS} = 10 Vdc, I _D = 200 mAdc)		100	-	μmhos
	C _{iss}	_	60	pF
$(V_{DS} = 25 \text{ V}, V_{GS} = 0,$ f = 1.0 MHz)	C _{oss}	-	25	
	C _{rss}	-	5.0	
S (Note 1)		•		•
(V _{DD} = 15 V, I _D = 500 mA,	t _{on}	-	10	ns
$R_G = 25 \Omega$, $R_L = 30 \Omega$, $V_{gen} = 10 V$)	t _{off}	-	10	
	$(V_{DS} = 48 \text{ Vdc}, V_{GS} = 0, T_J = 125^{\circ}\text{C})$ ward $(V_{GSF} = 15 \text{ Vdc}, V_{DS} = 0)$ $(V_{DS} = V_{GS}, I_D = 1.0 \text{ mAdc})$ the $(V_{GS} = 10 \text{ Vdc}, I_D = 0.5 \text{ Adc})$ $(V_{GS} = 4.5 \text{ Vdc}, I_D = 75 \text{ mAdc})$ $(V_{GS} = 4.5 \text{ Vdc}, I_D = 75 \text{ mAdc})$ $(V_{GS} = 4.5 \text{ Vdc}, V_{DS} = 10 \text{ Vdc})$ $(V_{DS} = 4.5 \text{ Vdc}, V_{DS} = 10 \text{ Vdc})$ $(V_{DS} = 10 \text{ Vdc}, I_D = 200 \text{ mAdc})$ $(V_{DS} = 10 \text{ Vdc}, I_D = 200 \text{ mAdc})$ $(V_{DS} = 25 \text{ V}, V_{GS} = 0, f = 1.0 \text{ MHz})$	(V _{DS} = 48 Vdc, V _{GS} = 0) (V _{DS} = 48 Vdc, V _{GS} = 0, T _J = 125°C) vard (V _{GSF} = 15 Vdc, V _{DS} = 0) (V _{DS} = V _{GS} , I _D = 1.0 mAdc) (V _{GS} = 10 Vdc, I _D = 0.5 Adc) (V _{GS} = 4.5 Vdc, I _D = 75 mAdc) (V _{GS} = 4.5 Vdc, I _D = 75 mAdc) (V _{GS} = 4.5 Vdc, I _D = 75 mAdc) (V _{GS} = 4.5 Vdc, V _{DS} = 10 Vdc) (V _{GS} = 4.5 Vdc, I _D = 200 mAdc) (V _{DS} = 10 Vdc, I _D = 200 mAdc) (V _{DS} = 25 V, V _{GS} = 0, f = 1.0 MHz) (V _{DD} = 15 V, I _D = 500 mA, to make the composition of the com	(V _{DS} = 48 Vdc, V _{GS} = 0) (V _{DS} = 48 Vdc, V _{GS} = 0, T _J = 125°C) vard (V _{GSF} = 15 Vdc, V _{DS} = 0) (V _{DS} = V _{GS} , I _D = 1.0 mAdc) (V _{DS} = V _{GS} , I _D = 1.0 mAdc) (V _{GS} = 10 Vdc, I _D = 0.5 Adc) (V _{GS} = 4.5 Vdc, I _D = 75 mAdc) (V _{GS} = 4.5 Vdc, I _D = 75 mAdc) (V _{GS} = 4.5 Vdc, I _D = 75 mAdc) (V _{GS} = 4.5 Vdc, V _{DS} = 10 Vdc) (V _{GS} = 4.5 Vdc, I _D = 200 mAdc) (V _{DS} = 10 Vdc, I _D = 200 mAdc) (V _{DS} = 10 Vdc, I _D = 200 mAdc) (V _{DS} = 10 Vdc, I _D = 200 mAdc) (V _{DS} = 25 V, V _{GS} = 0, C _{OSS} - C _{Crss} -	

^{1.} Pulse Test: Pulse Width $\leq 300~\mu s,~Duty~Cycle \leq 2.0\%.$

ORDERING INFORMATION

Device	Package	Shipping [†]
2N7000G	TO-92 (Pb-Free)	1000 Units / Bulk
2N7000RLRAG	TO-92 (Pb-Free)	2000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

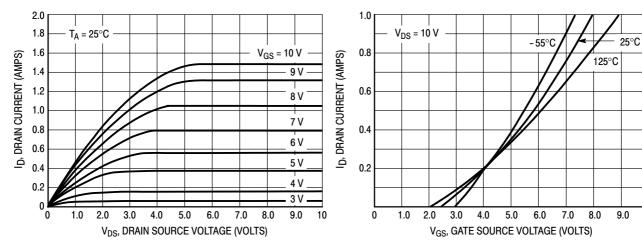


Figure 1. Ohmic Region

Figure 2. Transfer Characteristics

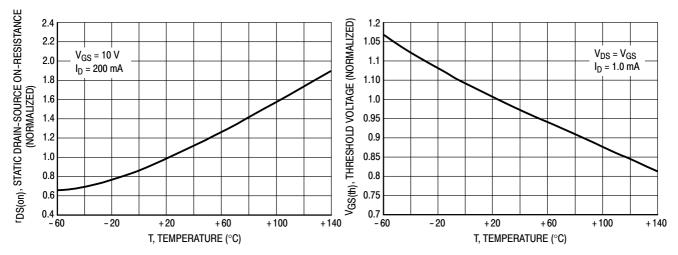
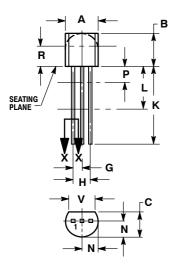


Figure 3. Temperature versus Static Drain-Source On-Resistance

Figure 4. Temperature versus Gate Threshold Voltage

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**



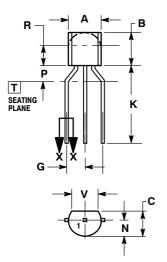
STRAIGHT LEAD **BULK PACK**



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
 CONTOUR OF PACKAGE BEYOND
- DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN PAND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
V	3.43		

STYLE 22: PIN 1. SOURCE GATE

DRAIN

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